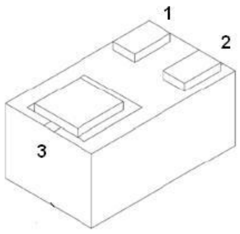
Schottky Barrier Diode

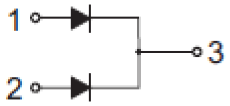
SKD0203N3 **DFN1006-3L**

Features

- Extremely Fast Switching Speed
- Low Forward Voltage

DFN1006-3L





Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
Working Peak Reverse Voltage	V_{RWM}	30	V
RMS Reverse Voltage	$V_{R(RMS)}$	21	V
Average Forward Current	I_O	200	mA
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I_{FSM}	600	mA
Repetitive Peak Forward Current @ t≤1s,δ≤0.5	I_{FRM}	300	mA
Power Dissipation	P_D	100	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	1000	℃/mW
Junction Temperature	T_J	125	℃
Storage Temperature	T_{STG}	-55 to +150	℃

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Electrical Characteristics (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Reverse Voltage	$V_{(BR)}$	I_R = 500μA	30	--	--	V
Reverse Current	I_R	V_R = 30V	--	--	2	μA
Forward Voltage	V_F	I_F = 100mA	--	--	0.7	
Total capacitance	C_{tot}	V_R = 1V, f = 1MHz	--	--	10	pF
Reverse recovery time	t_{rr}	I_F = I_R = 10mA, $I_{R(REC)}$ = 1mA	--	--	5	ns

Typical Characteristic Curves

Fig1. Forward Characteristics

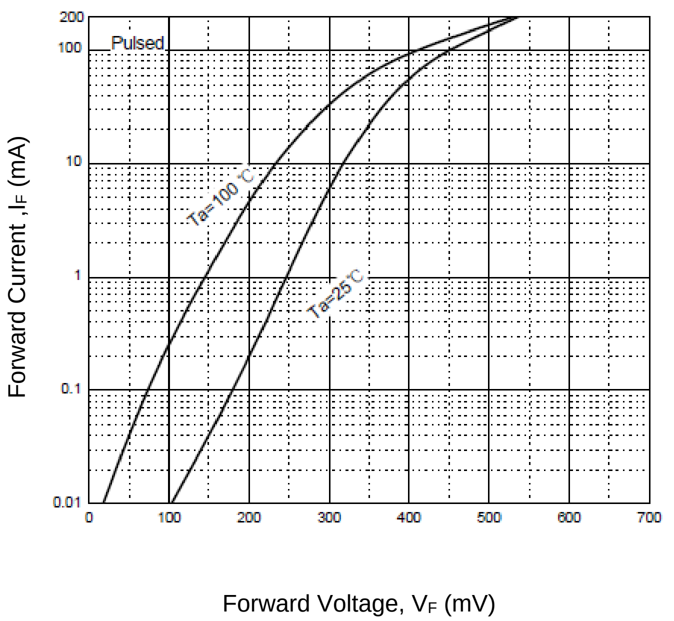
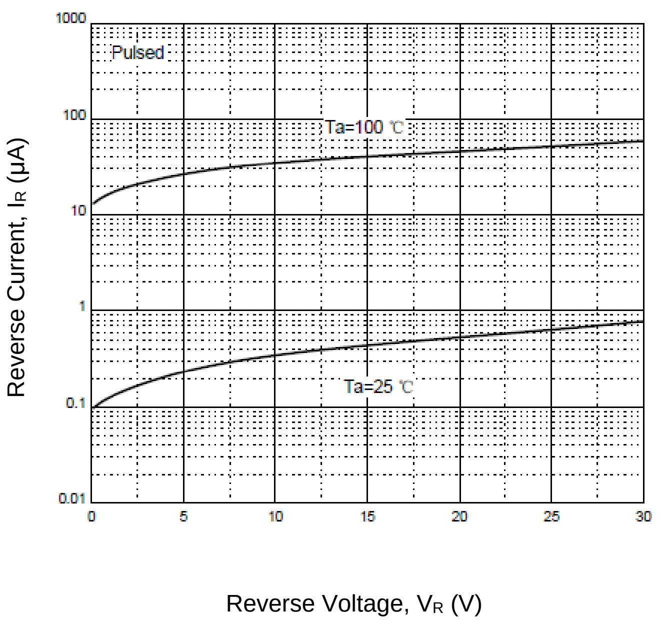


Fig2. Reverse Characteristics



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Typical Characteristic Curves (Continue)

Fig3. Capacitance Characteristics

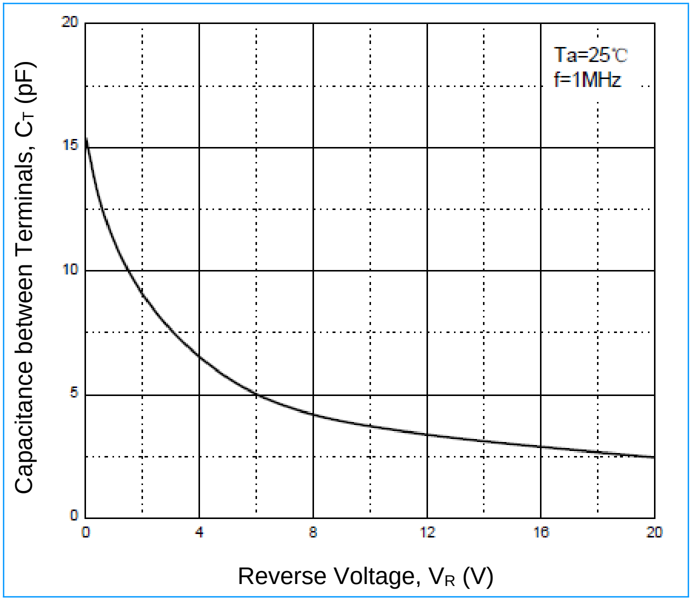
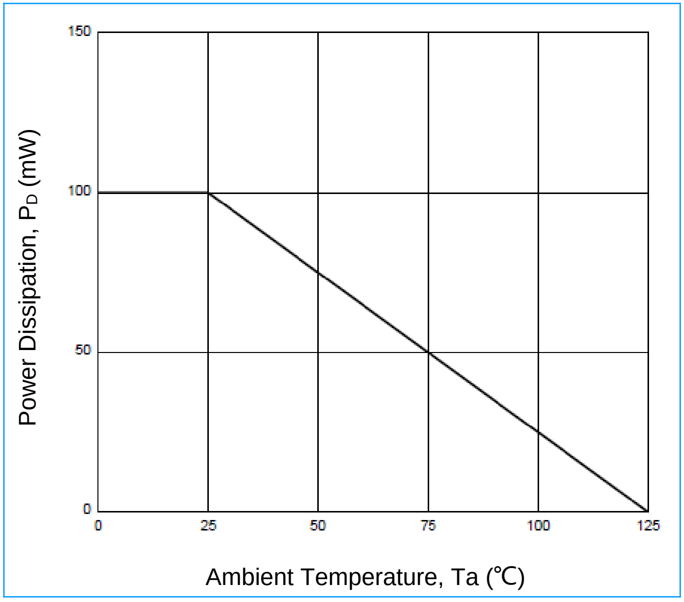
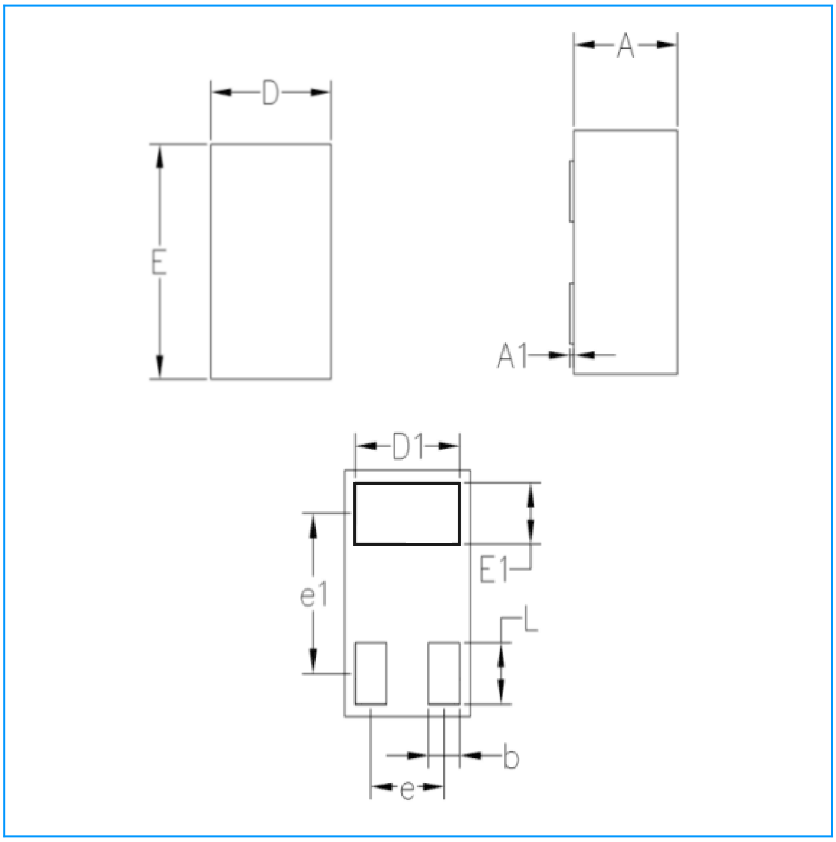


Fig4. Power Derating Curve



DFN1006-3L Package Outline Dimensions



Symbol	Dimensions in Millimeters		
	Min	Nom	Max
A	0.45	0.50	0.55
A1	0.00	--	0.05
D	0.55	0.60	0.65
E	0.95	1.00	1.05
D1	0.45	0.50	0.55
E1	0.20	0.25	0.30
L	0.20	0.25	0.30
b	0.10	0.15	0.20
e	0.35 BSC		
e1	0.65 BSC		

Ordering Information

Part Number	Package	Quantity
SKD0203N3	DFN1006-3L	10000PCS